

### FDG6302P Dual P-Channel, Digital FET

### **General Description**

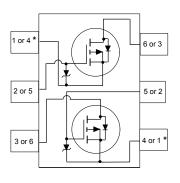
These dual P-Channel logic level enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs.

### **Features**

- -25 V, -0.14 A continuous, -0.4 A peak.  $R_{\rm DS(ON)} = 10~\Omega~@~V_{\rm GS} = -4.5~{\rm V}, \\ R_{\rm DS(ON)} = 13~\Omega~@~V_{\rm GS} = -2.7~{\rm V}.$
- Very low level gate drive requirements allowing direct operation in 3 V circuits (V<sub>GS(th)</sub> < 1.5 V).</li>
- Gate-Source Zener for ESD ruggedness (>6kV Human Body Model).
- Compact industry standard SC70-6 surface mount package.







<sup>\*</sup>The pinouts are symmetrical; pin 1 and 4 are interchangeable.

Units inside the carrier can be of either orientation and will not affect the functionality of the device.

### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	FDG6302P	Units	
V <sub>DSS</sub>	Drain-Source Voltage	-25	V	
V <sub>GSS</sub>	Gate-Source Voltage	-8	V	
I <sub>D</sub>	Drain/Output Current - Continuous	-0.14	A	
	- Pulsed	-0.4		
$P_{D}$	Maximum Power Dissipation (Note 1)	0.3	W	
T <sub>J</sub> ,T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 150	°C	
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100 pF / 1500 $\Omega$ )	6.0	kV	
THERMA	L CHARACTERISTICS		·	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	415	°C/W	

Symbol	Parameter	Conditions	Min	Тур	Max	Units
FF CHAR	ACTERISTICS					
3V <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-25			V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	I <sub>D</sub> = -250 μA, Referenced to 25°C		-19		mV /°C
OSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V			-1	μA
		T <sub>J</sub> = 55°C			-10	μA
GSS	Gate - Body Leakage Current	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 0 V			-100	nA
	CTERISTICS (Note 2)					
/ <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.65	-0.9	-1.5	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp.Coefficient	I <sub>D</sub> = -250 μA, Referenced to 25°C		2		mV / °C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_{D} = -0.14 \text{ A}$		7.3	10	Ω
		T <sub>J</sub> =125°C		11	17	1
		$V_{GS} = -2.7 \text{ V}, I_D = -0.05 \text{ A}$		10.4	13	1
D(ON)	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \ V_{DS} = -5 \text{ V}$	-0.14			Α
FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, I_{D} = -0.14 \text{ A}$		0.12		S
DYNAMIC CI	HARACTERISTICS					
iss	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		12		pF
oss	Output Capacitance	f = 1.0 MHz		7		pF
O <sub>rss</sub>	Reverse Transfer Capacitance			1.5		pF
WITCHING	CHARACTERISTICS (Note 2)					
D(on)	Turn - On Delay Time	$V_{DD} = -5 \text{ V}, I_{D} = -0.25 \text{ A},$		5	12	ns
	Tum - On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		8	16	ns
D(off)	Tum - Off Delay Time			9	18	ns
f	Tum - Off Fall Time			5	10	ns
$Q_g$	Total Gate Charge	$V_{DS} = -5 \text{ V}, I_{D} = -0.14 \text{ A},$ $V_{GS} = -4.5 \text{ V}$		0.22	0.31	nC
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = -4.5 V		0.12		nC
$Q_{gd}$	Gate-Drain Charge			0.05		nC
RAIN-SOU	RCE DIODE CHARACTERISTICS AND MAXIN	IUM RATINGS				
3	Maximum Continuous Source Current				-0.25	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -0.25 \text{ A (Note 2)}$		-0.8	-1.2	V

Notes:

1. R<sub>g,xi</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>g,xi</sub> is guaranteed by design while  $R_{jch}$  is determined by the user's board design.  $R_{joh} = 415^{\circ}$ C/W on minimum pad mounting on FR-4 board in still air. 2. Pulse Test: Pulse Width  $\leq 300\mu$ s, Duty Cycle  $\leq 2.0\%$ .

### **Typical Electrical Characteristics**

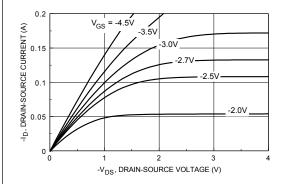


Figure 1. On-Region Characteristics.

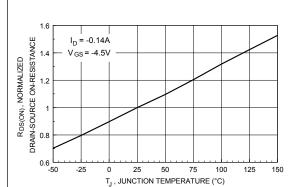


Figure 3. On-Resistance Variation with Temperature.

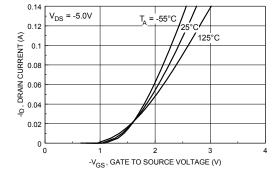


Figure 5. Transfer Characteristics.

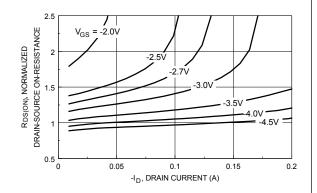


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

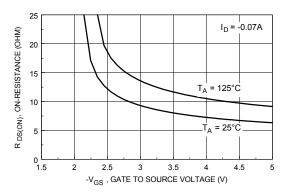


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

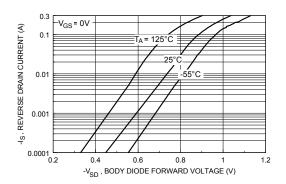


Figure 6. Body Diode Forward Voltage
Variation with Source Current
and Temperature.

### **Typical Electrical Characteristics**

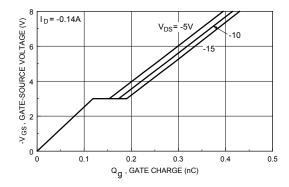


Figure 7. Gate Charge Characteristics.

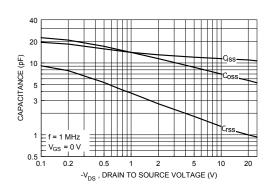
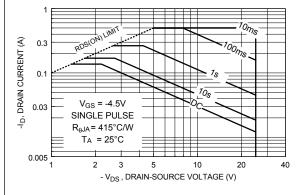


Figure 8. Capacitance Characteristics.



40 R<sub>6</sub>JA=415°C/W TA=25°C TA=2

Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

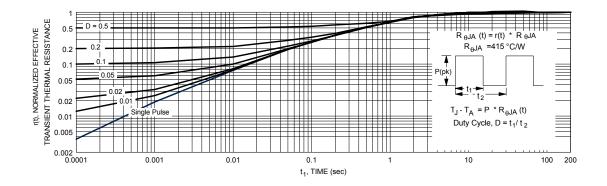
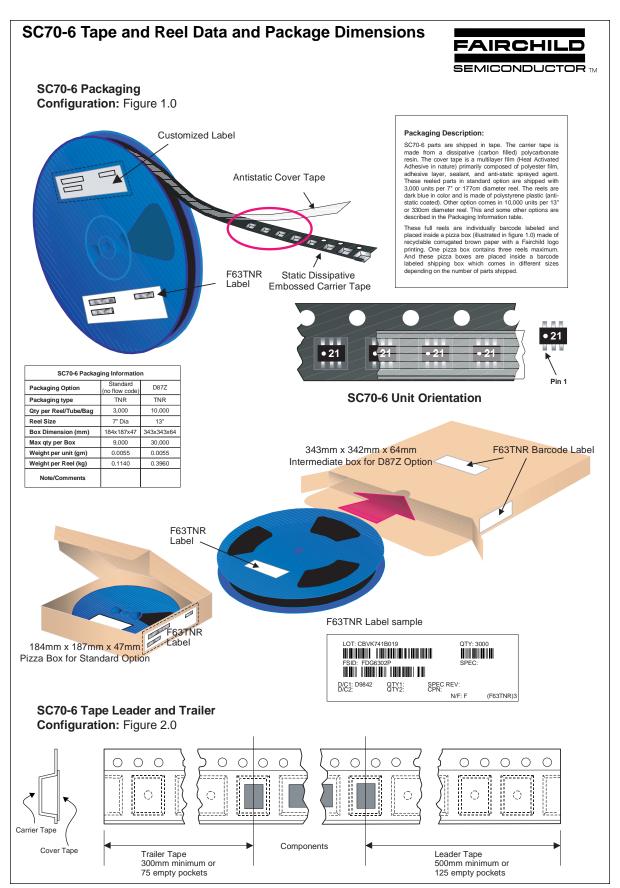


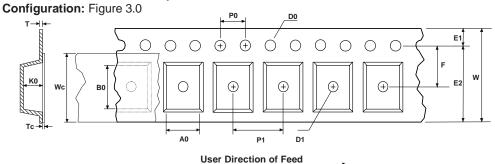
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in note 1. Transient thermalresponse will change depending on the circuit board design.





### **SC70-6 Embossed Carrier Tape**

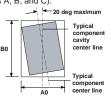


Dimensions are in millimeter														
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SC70-6 (8mm)	2.24 +/-0.10	2.34 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.20 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

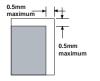


Sketch A (Side or Front Sectional View)
Component Rotation



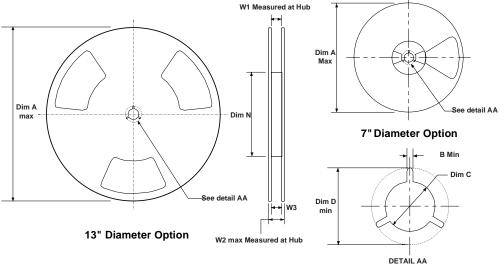
Sketch B (Top View)

Component Rotation



Sketch C (Top View)
Component lateral movement

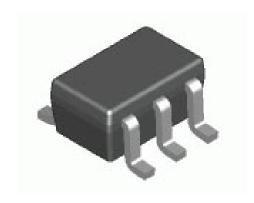
SC70-6 Reel Configuration: Figure 4.0

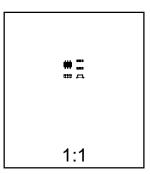


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	0.512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	0.512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

## SC70-6 Tape and Reel Data and Package Dimensions, continued

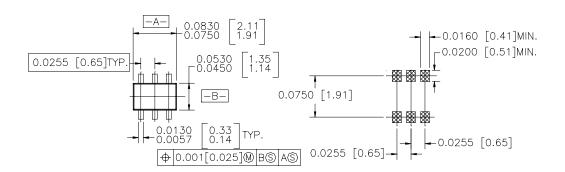
# SC70-6 (FS PKG Code 76)



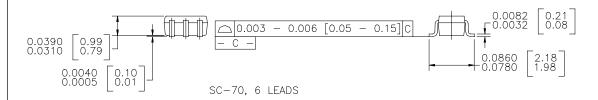


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0055



### LAND PATTERN RECOMMENDATION



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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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